

Ultra-Low Capacitance TVS Protection
Dec 2021 Ver. 1.1

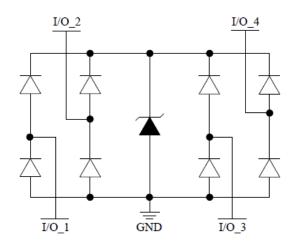
Description

HWET03346P is an ultra-low - capacitance Transient Voltage Suppressor (TVS) designed to provide electrostatic discharge (ESD) protection for high-speed data interfaces. With Maximum capacitance0.65pF only, HWET03346P is designed to protect parasitic - sensitive systems against over-voltage and over-current transient events. It complies with IEC 61000-4-2 (ESD), Level 4 (±15kV air, ±8kV contact discharge), IEC 61000-4-4 (electrical fast transient - EFT) (40A, 5/50 ns), very fast charged device model (CDM) ESD and cable discharge event (CDE), etc. HWET03346P uses ultra-small DFN-10L package. Each HWET03346P device can protect four high-speed data lines. The combined features of ultra-low capacitance, ultra-small size and high ESD robustness make HWET03346P ideal for high-speed data ports and high-frequency lines (e.g., HDMI & DVI) applications. The low clamping voltage of the HWET03346P guarantees a minimum stress on the protected IC.

Mechanical Characteristics

- DFN-10L package
- Flammability Rating: UL 94V-0
- Marking: Part number
- Packaging: Tape and Reel

Circuit Diagram



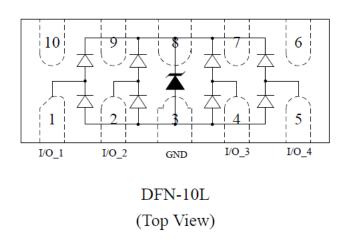
Features

- Transient protection for high-speed data lines
 IEC 61000-4-2 (ESD) ±25kV (Air)
 ±17kV (Contact)
 IEC 61000-4-4 (EFT) 40A (5/50 ns)
 Cable Discharge Event (CDE)
- Package optimized for high-speed lines
- Ultra-small package (2.5mm*1.0mm*0.55mm)
- Protects four data lines
- Low capacitance: 0.65pF Maximum
- Low leakage current: 0.1µ A @ VRWM (Max.)
- Low clamping voltage
- Each I/O pin can withstand over 1000 ESD strikes for ±8kV contact discharge
- ROHS compliant

Applications

- Serial ATA
- PCI Express
- Desktops, Servers and Notebooks
- MDDI Ports
- USB2.0/3.0 Power and Data Line Protection
- Display Ports
- High Definition Multi-Media Interface (HDMI)
- Digital Visual Interfaces (DVI)

Pin Configuration





■Electrical characteristics (Ta = 25 °C)

Symbol	Test Condition	Minimum	Typical	Maximum	Units
V _{RWM}				3.3	V
I_R	$V_{RWM} = 3.3V, T = 25^{\circ}C$		0.01	0.1	μΑ
V _{t1}	$I_{t1} = 100uA$	6		8	V
V_h	$I_h \ge 40 \text{mA}$	3		5.5	V
$V_{\rm C}$	I_{PP} = 3.0A, t_p = 8/20 μ s		8	10	V
Cesd	$V_R = 0V$, $f = 1MHz$ Between I/O and GND			0.65	pF
Cesd	$V_R = 0V$, $f = 1MHz$ Between I/O and I/O			0.4	pF

Absolute Maximum Rating

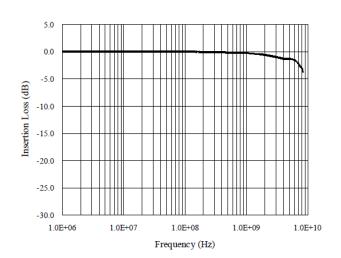
Symbol	Parameter	Value	Units	
I PP	Peak Pulse Current(tp=8/20us)	3	А	
Vesd	ESD per IEC 61000-4-2(Air)	±25	14) /	
	ESD per IEC 61000-4-2 (Contact)	±17	kV	
Торт	Operating Temperature	-55/+125	°C	
Tstg	Storage Temperature	-55/+150	°C	



TLP Measurement of I/O to GND

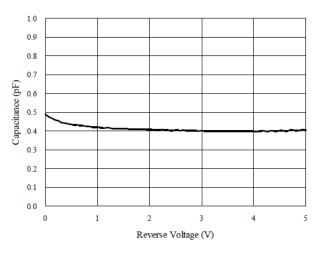
20 18 16 14 12 10 8 6 4 2 0 0 1 2 3 4 5 6 7 8 TLP Voltage (V)

Insertion Loss S21 of I/O to GND

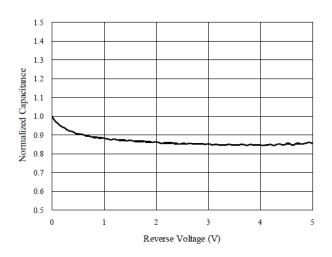


Capacitance vs. Voltage of I/O to GND (f = 1MHz)

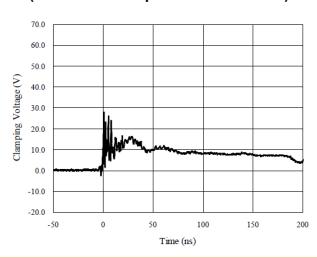
Capacitance vs. Reverse Voltage



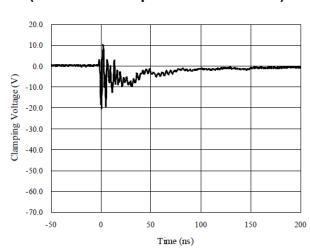
Normalized Capacitance vs. Reverse Voltage



ESD Clamping of I/O to GND (+8kV Contact per IEC 61000-4-2)



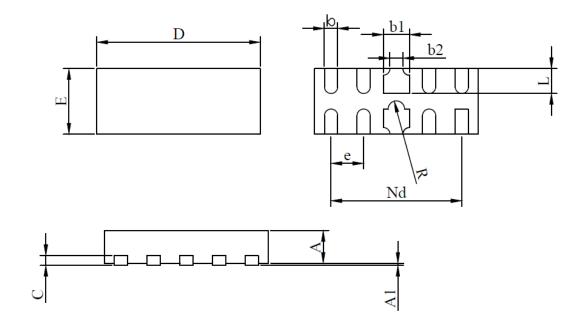
ESD Clamping of I/O to GND (-8kV Contact per IEC 61000-4-2)



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Package Outline

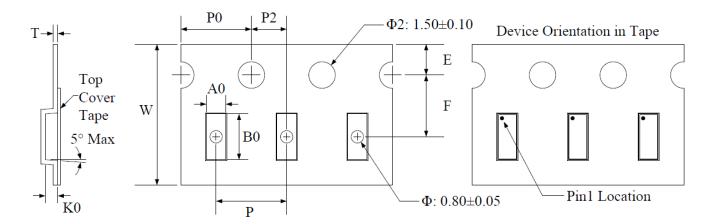
- DFN-10L package
- Thermally-Enhanced
- MSL-1 Level



SYMBO	MILLIMETER					
L	MIN	NOM	MAX			
D	2.45	2.50	2.55			
Е	0.95	1.00	1.05			
b1	0.35	0.40	0.45			
b2	0.20REF					
b	0.15	0.20	0.25			
L	0.33	0.38	0.43			
Nd	2.00REF					
e	0.50REF					
R	0.10	0.125	0.15			
A	0.45	0.50	0.55			
С	0.15REF					
A1	0.00	-	0.05			



Tape and Reel Specification



Symbol	W	A0	В0	K0	E	F	P	P0	P2	T
Dimensions (mm)	8.00+0.3 -0.1	1.23±0.05	2.7±0.05	0.7±0.05	1.75±0.1	3.5±0.05	4.0±0.1	4.0±0.1	2.0±0.05	0.25±0.02